

Notice of References Cited		Application/Control No. 10/784,947	Applicant(s)/Patent Under Reexamination TOTSUKA ET AL.	
		Examiner Bac H. Au	Art Unit 2822	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,592,771	07-2003	Yamanaka et al.	216/63
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Spruytte, Sylvia G.; MBE Growth on Nitride-Arsenide Materials for Long Wavelength Optoelectronics; 3 December 1999; MRS Internet J. Nitride Semicond. Res. 5S1, W8.4 (2000).
	V	Vaudo, R. P.; Atomic-nitrogen production in a radio-frequency plasma source; 1 November 1993; Optical Society of America, Optics Letter; Vol.18, No.21.
	W	Blant, A. V.; Nitrogen species from radio frequency plasma sources used for molecular beam epitaxy growth of GaN; 3 September 1999; Plasma Sources Sci. Technol. 9 (2000) 12-17.
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.